

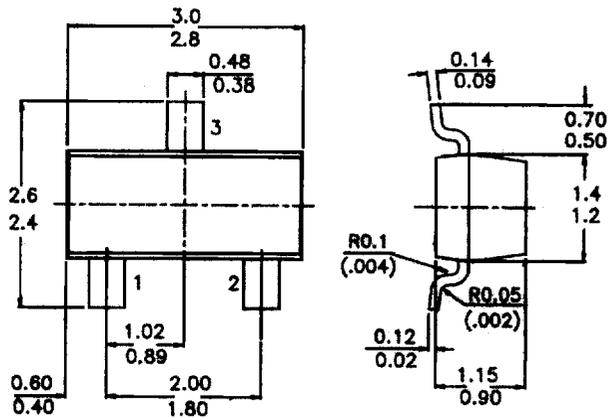
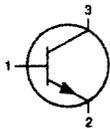
VHF/UHF TRANSISTOR

N-P-N transistor

Marking  
CMBT918 = 3B

PACKAGE OUTLINE DETAILS  
ALL DIMENSIONS IN mm

Pin configuration  
1 = BASE  
2 = EMITTER  
3 = COLLECTOR



ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)	$-V_{CB0}$	max.	30 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	15 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	3 V
Collector current (d.c.)	$-I_C$	max.	350 mA
Total power dissipation at $T_{amb} = 25^\circ\text{C}$	$P_{tot}$	max	225 mW
D.C. current gain	$h_{FE}$	min.	20
$-I_C = 3 \text{ mA}; -V_{CE} = 1 \text{ V}$			

RATINGS (at  $T_A = 25^\circ\text{C}$  unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)	$-V_{CB0}$	max.	30 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	15 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	3 V
Collector current (d.c.)	$-I_C$	max.	350 mA

Total power dissipation at $T_{amb} = 25^{\circ}\text{C}$	$P_{tot}$	max	225	mW
Storage temperature	$T_{stg}$		-55 to +150	$^{\circ}\text{C}$
Junction temperature	$T_j$	max.	150	$^{\circ}\text{C}$

**THERMAL CHARACTERISTICS**

$T_j = P (R_{th\ j-t} + R_{th\ s-a}) + T_{ar:b}$

Thermal resistance

from junction to ambient	$R_{th\ j-a}$		556	$^{\circ}\text{C}/\text{mW}$
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**CHARACTERISTICS (at  $T_A = 25^{\circ}\text{C}$  unless otherwise specified)**

Collector-emitter breakdown voltage $-I_C = 3\text{ mA}; -I_B = 0$	$-V_{(BR)CEO}$	min.	15	V
Collector-base breakdown voltage $-I_C = 1\ \mu\text{A}; -I_E = 0$	$-V_{(BR)CBO}$	min.	30	V
Emitter-base breakdown voltage $-I_E = 10\ \mu\text{A}; -I_C = 0$	$-V_{(BR)EBO}$	min.	3	V
Collector cut-off current $-V_{CB} = 15\text{ V}; -I_E = 0$	$-I_{CBO}$	max.	50	nA
Output capacitance at $f = 1\text{ MHz}$ $-V_{CB} = 10\text{ V}; I_E = 0$	$C_c$	max.	1.7	pF
Input capacitance at $f = 1\text{ MHz}$ $-V_{EB} = 0.5\text{ V}; I_C = 0$	$C_e$	max.	2	pF
Saturation voltages $-I_C = 10\text{ mA}; -I_B = 1\text{ mA}$	$-V_{CEsat}$	max.	0.4	V
	$-V_{BEsat}$	max.	1	V
D.C. current gain $-I_C = 3\text{ mA}; -V_{CE} = 1\text{ V}$	$h_{FE}$	min.	20	
Noise figure at $R_S = 50\ \Omega$ $-I_C = 1\text{ mA}; -V_{CE} = 6\text{ V}$ $f = 60\text{ MHz}$	NF	max.	6	dB
Transition frequency $V_{CE} = 10\text{ V}; I_C = 4\text{ mA}; f = 100\text{ MHz}$	$f_T$	min.	600	MHz